	1				
	L#	Hits	Search Text	DBs	Time Stamp
1	L1	6147 2	ono	USPAT; EPO; JPO	2000/11/17 16:23
2	L5	34	(reoxidized or re-oxidized) near5 nitride	JPO	2000/11/17 16:24
3	L9	0	5 and (wet adj (oxide or oxidation))	USPAT; EPO; JPO.	2000/11/17 16:30
4	L13	5	5 and steam	USPAT; ' EPO; JPO	2000/11/17 16:30
5	L25	804	1 with gate	USPAT; EPO; JPO	2000/11/17 16:29
6	L29	34	25 and (wet adj (oxide or oxidation))	USPAT; EPO; JPO	2000/11/17 18:06
7	L33	29	25 and water	USPAT; EPO; JPO	2000/11/17 18:06
8	L37	55	25 and steam	USPAT; EPO; JPO	2000/11/17 18:06
9	L41	3	25 and (pyrogenic adj (oxide or oxidation))	USPAT; EPO; JPO	2000/11/17 18:06
10	L21	3	5 and water	USPAT; / EPO; JPO	2000/11/17 16:32
11	L45	102	29 33 37 41	USPAT; EPO; JPO	2000/11/17 16:40
12	L49	5	45 and (RTN or nitridation)	USPAT; EPO; JPO	2000/11/17 17:47
13	L53	37	45 and ((heat\$3 or anneal\$3) near10 (nitrous oxide))	USPAT; EPO; JPO	2000/11/17 16:58
14	L57	1	45 and ((heat\$3 or anneal\$3) near10 (nitrous adj oxide))	USPAT; EPO; JPO	2000/11/17 16:59
15	L61	6	45 and ((heat\$3 or anneal\$3) near10 ("N.sub.2" adj O))	USPAT; EPO; JPO	2000/11/17 16:59
16	L65	1183	1 and (time near3 temperature)	USPAT; EPO; JPO	2000/11/17 17:51
17	L69	7976	(stabiliz\$3 or crystalliz\$3 or crystaliz\$3) near5 (oxide or dielectric)	USPAT; EPO; JPO	2000/11/17 17:54
18	L77	836	69 and steam	USPAT; EPO; JPO	2000/11/17 17:55
19	L81	1	69 and (pyrogenic adj (oxide or oxidation))	USPAT; EPO; JPO	2000/11/17 17:55

Page 1 (EKielin, 11/17/2000, EAST Version: 1.01.0015)

	L#	Hits	Search Text	DBs	Time Stamp
20	L73	25	69 and (wet adj (oxide or oxidation))	USPAT; EPO; JPO	2000/11/17 17:56
21	L85	95	1 and (wet adj (oxide or oxidation))	USPAT; EPO; JPO	2000/11/17 18:06
22	L89	8368	1 and water	USPAT; EPO; JPO	2000/11/17 18:08
23	L93	952	1 and steam	USPAT; EPO; JPO	2000/11/17 18:06
24	L97	7	1 and (pyrogenic adj (oxide or oxidation))	USPAT; EPO; JPO	2000/11/17 18:06
25	L101	681	(85 89 93 97) and (time near3 temperature)	USPAT; EPO; JPO	2000/11/17 18:09
26	L105	409	1 and (water near10 (oxide or oxidation))	USPAT; EPO; JPO	2000/11/17 18:09
27	L109	202	(85 105 93 97) and (time near3 temperature)	USPAT; EPO; JPO	2000/11/17 18:10

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PER		Z	Rapid thermal chemical vapor deposited oxides on N-type 6H-silicon carbide Sridevan, S.; Misra, V.; McLarty, P.K.; Baliga, B.J.; Wortman, J.J. IEEE Electron Device Letters Volume: 16 11, Nov. 1995, Page(s): 524 -526
PER			Formation of high-quality oxide/nitride stacked layers on rugged polysilicon electrodes by rapid thermal oxidation ltoh, S.; Lo, G.Q.; Kwong, D.L.; Mathews, V.K.; Fazan, P.C. Electron Devices, IEEE Transactions on Volume: 40 6, June 1993, Page(s): 1176-1178
CNF		7	STI TEOS densification for furnaces and RTP tools Baker, F.; Ballantine, A.; Fisch, E.; Hodge, W. Advanced Semiconductor Manufacturing Conference and Workshop, 1999 IEEE/SEMI, 1999, Page(s): 394-399
CNF			Control and stability of AlAs wet oxidation studied by in-situ optical monitoring in a low-pressure, low-temperature steam furnace Loehr, J.P.; Feld, S.A. Lasers and Electro-Optics Society Annual Meeting, 1998. LEOS '98. IEEE Volume: 2, 1998, Page(s): 110-111 vol.2
CNF			Real time, in situ measurement of film thickness with reflexion supported pyrometric interferometry (RSPI) Boebel, F.G.; Hertel, B.; Moller, H.; Preiss, W.; Ritter, G. Advanced Semiconductor Manufacturing Conference and Workshop. 1994 IEEE/SEMI, 1994, Page(s): 311-315